Not Recommended for New Design
Please Use ZTX749

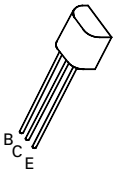
PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

FXT749

ISSUE 1 – FEB 94

FEATURES

* 25 Volt V_{CEO}
* 2 Amp continuous current
* Low saturation voltage
* P_{tot}= 1 Watt



E-Line
TO92 Compatible

REFER TO ZTX749 FOR GRAPHS

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-6	A
Continuous Collector Current	I_C	-2	A
Power Dissipation at T_{amb}=25°C	P_{tot}	1	W
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +200	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-35			V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-25			V	I_C=-10mA, I_B=0*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	I_E=-100μA, I_C=0
Collector Cut-Off Current	I_{CBO}			-0.1 -10	μA μA	V_{CB}=-30V V_{CB}=-30V,T_{amb}=100°C
Emitter Cut-Off Current	I_{EBO}			-0.1	μA	V_{EB}=-4V, I_E=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.12 -0.23	-0.3 -0.5	V V	I_C=-1A, I_B=-100mA* I_C=-2A, I_B=-200mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	-1.25	V	I_C=-1A, I_B=-100mA*
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.8	-1	V	IC=-1A, V_{CE}=-2V*
Static Forward Current Transfer Ratio	h_{FE}	70 100 75 15	200 200 150 50	300		I_C=-50mA, V_{CE}=-2V* I_C=-1A, V_{CE}=-2V* I_C=-2A, V_{CE}=-2V* I_C=-6A, V_{CE}=-2V*
Transition Frequency	f_T	100	160		MHz	I_C=-100mA, V_{CE}=-5V f=100MHz
Output Capacitance	C_{obo}			100	pF	V_{CB}=-10V, f=1MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%